

**REMARKS**

At the outset, the Examiner is thanked for the thorough review and consideration of the subject application. The Office Action of May 12, 2003 has been received and contents carefully reviewed.

By this Amendment, Applicants amend claims 41 and 55. Accordingly, claims 41-56 are currently pending in the present application. Reexamination and reconsideration of the application in view of the following remarks are respectfully requested.

In the Office Action, the Examiner objected to the drawings due to copy machine marks; and rejected claims 41-56 under 35 U.S.C. § 103(a) as being unpatentable over Yamaguchi et al. (U.S. Patent No. 5,897,346). Applicants respectfully traverse this rejection.

Applicants are submitting herewith Replacement sheet including Fig. 1A - 2C replacing all of the original drawings. No new matter has been added into the drawings.

Claim 41 is allowable over the cited references in that claim 41 recites a combination of elements including, for example, "forming an impurity region by implanting impurity ions to said excited region while the excited region remains in an excited state, whereby a post heat treatment for activation of the impurity ions is eliminated from the method of fabricating the thin film transistor." None of the cited references, singly or in combination, teaches or suggests at least this feature of the claimed invention. Accordingly, Applicants respectfully submit that claim 41 and claims 42-54, which depend therefrom, are allowable over the cited references.

Claim 55 is allowable over the cited references in that claim 55 recites a combination of elements including, for example, "forming an impurity region by implanting impurity ions to said excited region while the excited region remains in an excited state, wherein the activation of said impurity ions implanted occurs as the step of said implanting impurity ions is performed." None of the cited references, singly or in combination, teaches or suggests at least this feature of the claimed invention. Accordingly, Applicants respectfully submit that claim 55 and claim 56, which depends therefrom, are allowable over the cited references.

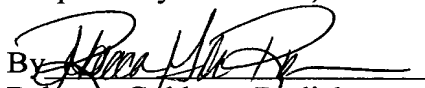
Moreover, Applicants respectfully submit that while Yamaguchi may disclose implantation of hydrogen ions, Yamaguchi does not disclose or suggest the claimed features of the present invention. For example, with respect to claim 1, Yamaguchi still needs a post heat treatment for activation of the impurity ions, which in the claimed invention, is eliminated from the method of fabricating the thin film transistor.

Applicants believe the foregoing amendments place the application in condition for allowance and early, favorable action is respectfully solicited. If the Examiner deems that a telephone conference would further the prosecution of this application, the Examiner is invited to call the undersigned attorney at the telephone number (202) 496 - 7500. All correspondence should continue to be sent to the below-listed address.

If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time, or any other fees required to complete the filing of this response, may be charged to Deposit Account No. 50-0911. Please credit any overpayment to deposit Account No. 50-0911.

Dated: October 1, 2003

Respectfully submitted,

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Attachments



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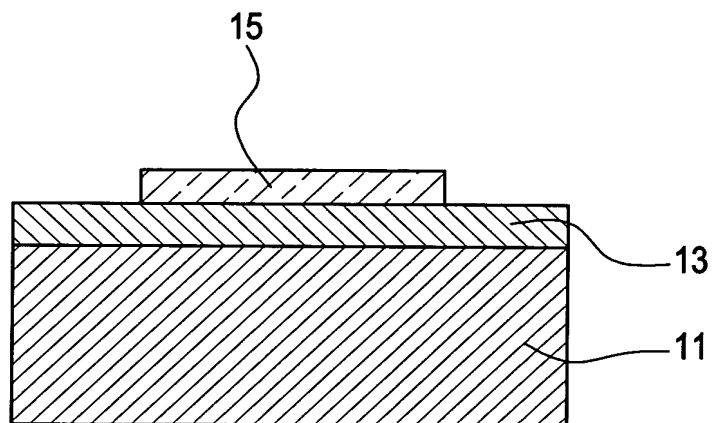


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## Replacement sheet

**FIG. 1A**  
PRIOR ART



**FIG. 1B**  
PRIOR ART

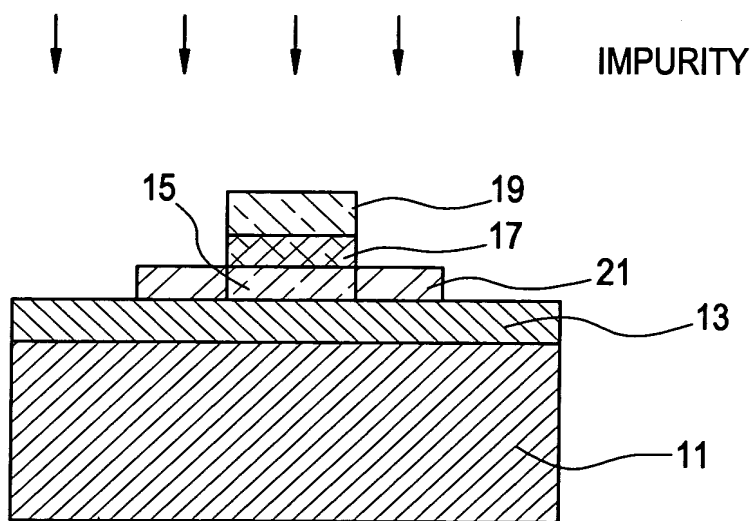


FIG. 1C  
PRIOR ART

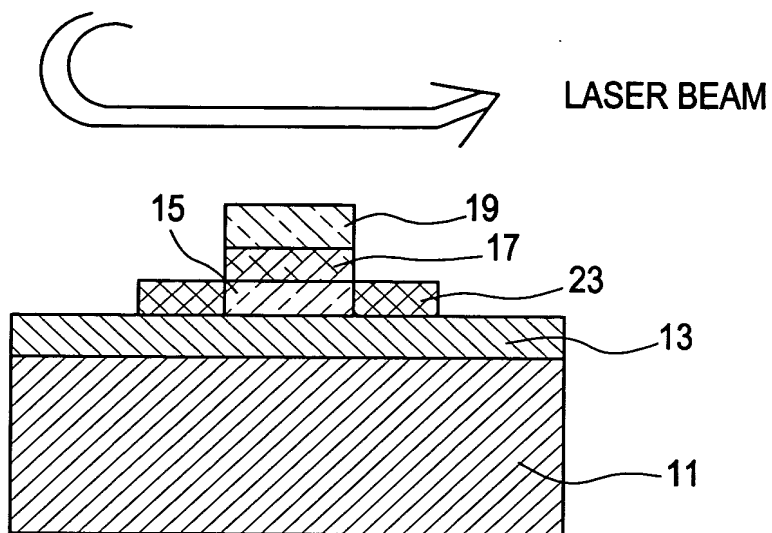
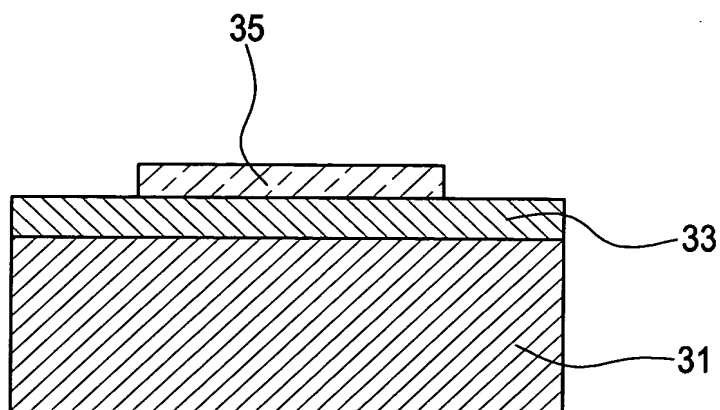


FIG. 2A





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FIG. 2B

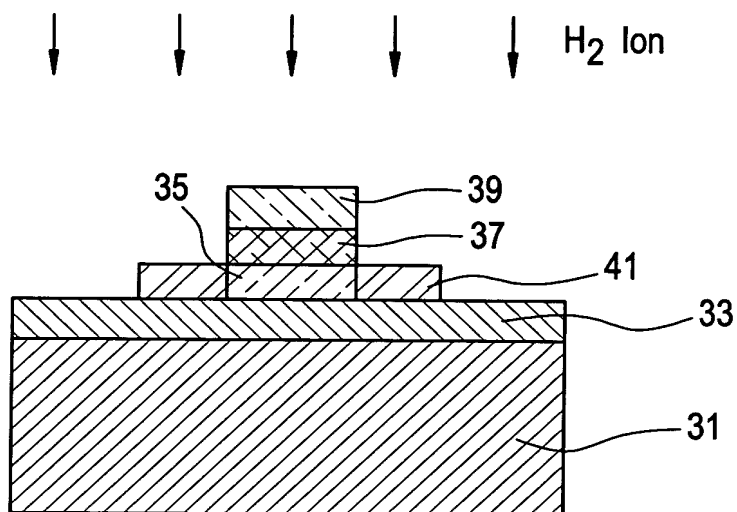


FIG. 2C

